

P-Ch MOSFET

#### **General Description**

The WST3035 is the highest performance trench P-Ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WST3035 meet the RoHS and Green Product requirement, with full function reliability approved.

#### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

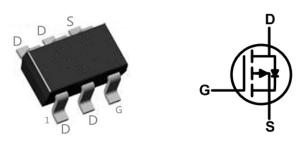
## **Product Summery**

BVDSS	RDSON	ID
-30V	50mΩ	-4.4A

#### Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

#### SOT- 23-6L Pin Configuration



#### **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units	
V <sub>DS</sub>	Drain-Source Voltage	-30	V	
V <sub>GS</sub>	Gate-Source Voltage	±20	V	
I <sub>D</sub> @T <sub>C</sub> =25℃	Continuous Drain Current, V <sub>GS</sub> @ -4.5V <sup>1</sup>	-4.4	A	
I <sub>D</sub> @T <sub>C</sub> =70℃	Continuous Drain Current, V <sub>GS</sub> @ -4.5V <sup>1</sup>	-3.0	A	
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	-14	A	
P <sub>D</sub> @T <sub>A</sub> =25℃	Total Power Dissipation <sup>3</sup>	1	W	
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	

#### **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit	
R <sub>eja</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>		125	°C/W	
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>		80	°C/W	



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#### Electrical Characteristics (T<sub>J</sub>=25<sup>1</sup>C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA	-30			V
$\triangle BV_{DSS} / \triangle T_J$	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25 $^\circ\!\mathrm{C}$ , I_D=-1mA		-0.014		V/℃
Б	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V , I <sub>D</sub> =-3A		50	60	mΩ
R <sub>DS(ON)</sub>		V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-2A		73	90	
V <sub>GS(th)</sub>	Gate Threshold Voltage		-0.5	-1.0	-2.5	V
$ riangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	$V_{GS}=V_{DS}$ , $I_{D}=-250$ uA		3.95		mV/℃
	Drein Course Lockage Current	$V_{DS}$ =-24V , $V_{GS}$ =0V , T <sub>J</sub> =25 $^{\circ}$ C			-1	uA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-24V , V <sub>GS</sub> =0V , T <sub>J</sub> =55℃			-5	
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}=\pm20V$ , $V_{DS}=0V$			±100	nA
gfs	Forward Transconductance	V <sub>DS</sub> =-5V , I <sub>D</sub> =-3A		12.8		S
Qg	Total Gate Charge (-4.5V)	V <sub>DS</sub> =-15V , V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-3A		12	14.3	
Q <sub>gs</sub>	Gate-Source Charge			1.92	2.6	nC
$Q_gd$	Gate-Drain Charge			3.3	4.3	
T <sub>d(on)</sub>	Turn-On Delay Time			5.9	11.2	
Tr	Rise Time	V <sub>DD</sub> =-15V ,		42	73	20
T <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS}$ =-4.5V , R <sub>G</sub> =3.3 $\Omega$ ,		34	67	ns
T <sub>f</sub>	Fall Time	I <sub>D</sub> =-3A		19	36	
C <sub>iss</sub>	Input Capacitance			895		
Coss	Output Capacitance	V <sub>DS</sub> =-15V , V <sub>GS</sub> =0V , f=1MHz		134		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			120		

#### **Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
ls	Continuous Source Current <sup>1,4</sup>				-1	А
I <sub>SM</sub>	Pulsed Source Current <sup>2,4</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			-14	А
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =-1A , T <sub>J</sub> =25℃			-1	V
t <sub>rr</sub>	Reverse Recovery Time			23		nS
Qrr	Reverse Recovery Charge	IF=-3A , dl/dt=100A/µs , T <sub>J</sub> =25 $^\circ \mathbb{C}$		7.2		nC

Note :

1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper,t<10sec.

2.The data tested by pulsed , pulse width  $\,\leq\,$  300us , duty cycle  $\,\leq\,$  2%

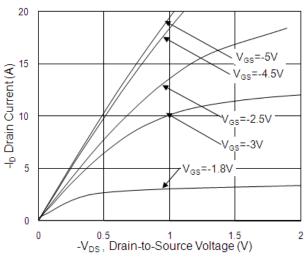
3. The power dissipation is limited by 150  $^\circ\!C$  junction temperature

4. The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications , should be limited by total power dissipation.



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**Typical Characteristics** 



**Fig.1 Typical Output Characteristics** 

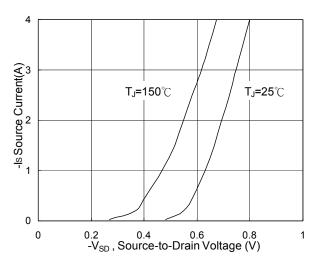
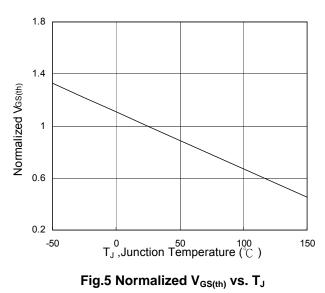
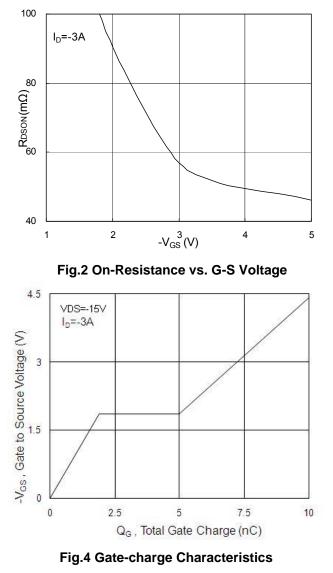


Fig.3 Forward Characteristics of Reverse





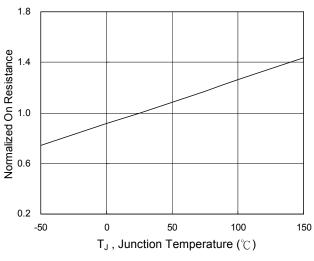
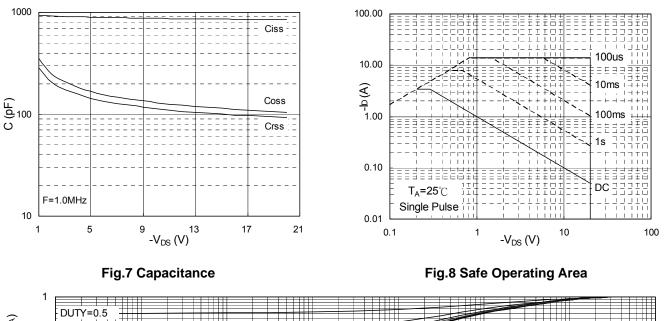
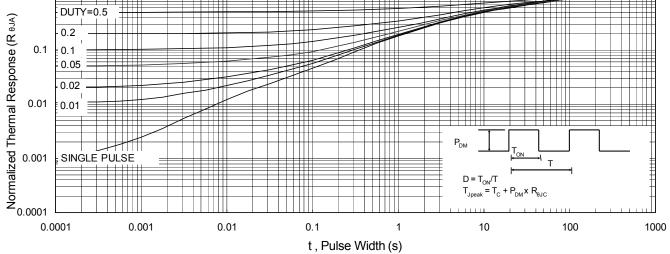


Fig.6 Normalized  $R_{\text{DSON}}$  vs.  $T_{\text{J}}$ 

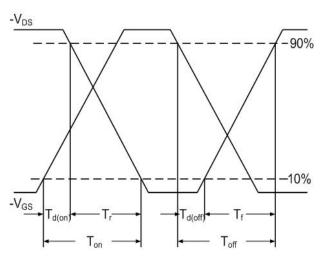


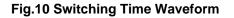
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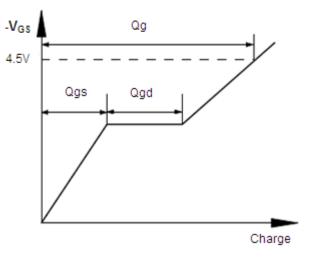




## Fig.9 Normalized Maximum Transient Thermal Impedance







#### Fig.11 Gate Charge Waveform



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